

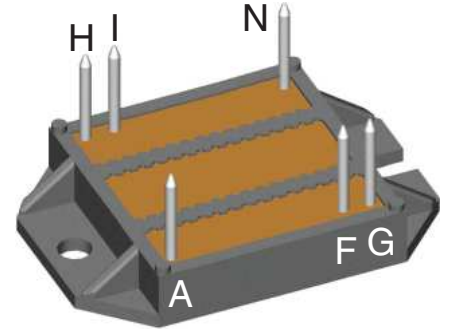
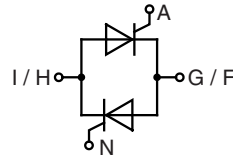
AC Controller Modules

$$I_{RMS} = 112 \text{ A}$$

$$I_{TAVM} = 51 \text{ A}$$

$$V_{RRM} = 1200/1600 \text{ V}$$

V_{RSM}	V_{RRM}	Typ
V_{DSM} V	V_{DRM} V	
1300	1200	MMO 140-12io7
1700	1600	MMO 140-16io7



Preliminary Data

Symbol	Conditions	Maximum Ratings	
I_{RMS}	$T_C = 85^\circ\text{C}$; 50-400 Hz (per single controller)	112	A
I_{TRMS}		81	A
I_{TAVM}	$T_C = 85^\circ\text{C}$; 180° sine	51	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz)	1000	A
	$V_R = 0$; $t = 8.3 \text{ ms}$ (60 Hz)	1070	A
I^2t	$T_{VJ} = 125^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz)	870	A
	$V_R = 0$; $t = 8.3 \text{ ms}$ (60 Hz)	930	A
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$; $f = 50 \text{ Hz}$; $t_p = 200 \mu\text{s}$; repetitive, $I_T = 50 \text{ A}$	100	A/ μs
	$V_D = \frac{2}{3} V_{DRM}$; $I_G = 0.45 \text{ A}$; $di_G/dt = 0.45 \text{ A}/\mu\text{s}$; non repetitive, $I_T = I_{TAVM}$	500	A/ μs
	$T_{VJ} = 125^\circ\text{C}$; $V_D = \frac{2}{3} V_{DRM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	V/ μs
P_{GM}	$T_{VJ} = 125^\circ\text{C}$; $t_p = 30 \text{ ms}$	10	W
	$I_T = I_{T(AV)M}$; $t_p = 300 \text{ ms}$	5	W
P_{GAVM}		0.5	W
V_{RGM}		10	V
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS; $t = 1 \text{ min}$	2500	V~
	$I_{ISOL} \leq 1 \text{ mA}$; $t = 1 \text{ s}$	3000	V~
M_d	Mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
Weight	Typical including screws	18	g

Features

- Thyristor controller for AC (circuit W1C acc. to IEC) for mains frequency
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

- Switching and control of single and three phase AC circuits
- Light and temperature control
- Softstart AC motor controller
- Solid state switches

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling
- High power density
- Small and light weight

Data according to IEC 60747 and refer to a single diode unless otherwise stated.

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IXYS reserves the right to change limits, test conditions and dimensions.

20200120c

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_D, I_R	$V_R / V_D = V_{RRM} / V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$	5 mA
V_T	$I_T = 150 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$	1.57 V
V_{T0}	For power-loss calculations only		0.85 V
r_t			5.60 mΩ
V_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	1.5 V
		$T_{VJ} = -40^\circ\text{C}$	1.9 V
I_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	100 mA
		$T_{VJ} = -40^\circ\text{C}$	200 mA
V_{GD}	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$	0.2 V
I_{GD}			1 mA
I_L	$t_p = 10 \mu\text{s};$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$	200 mA
I_H	$V_D = 6 \text{ V}; R_{GK} = \infty;$	$T_{VJ} = 25^\circ\text{C}$	100 mA
t_{gd}	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$	2 μs
R_{thJC}	per thyristor; DC current		0.80 K/W
R_{thCH}		0.12	K/W
R_{thJC}	per module		0.40 K/W
R_{thCH}		0.06	K/W
d_s	Creeping distance on surface		11.2 mm
d_A	Creepage distance in air		5.0 mm
a	Maximum allowable acceleration		50 m/s ²

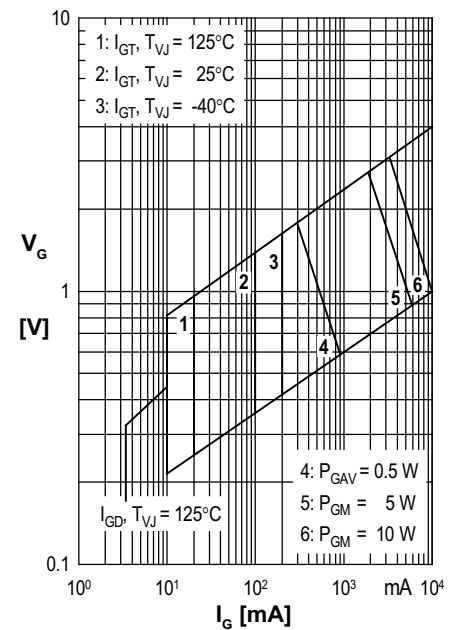


Fig. 1 Gate trigger characteristics

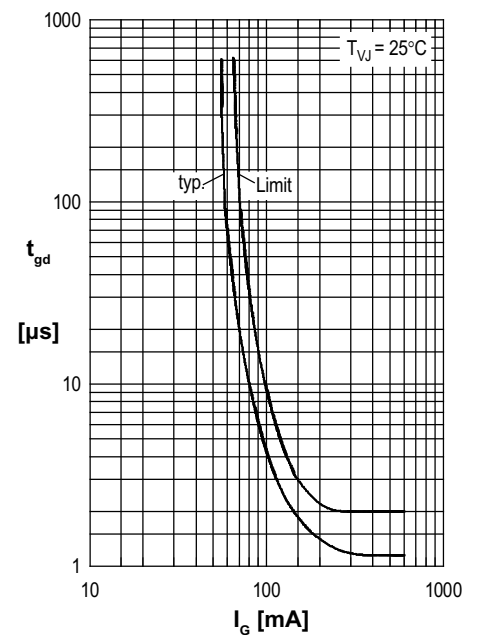
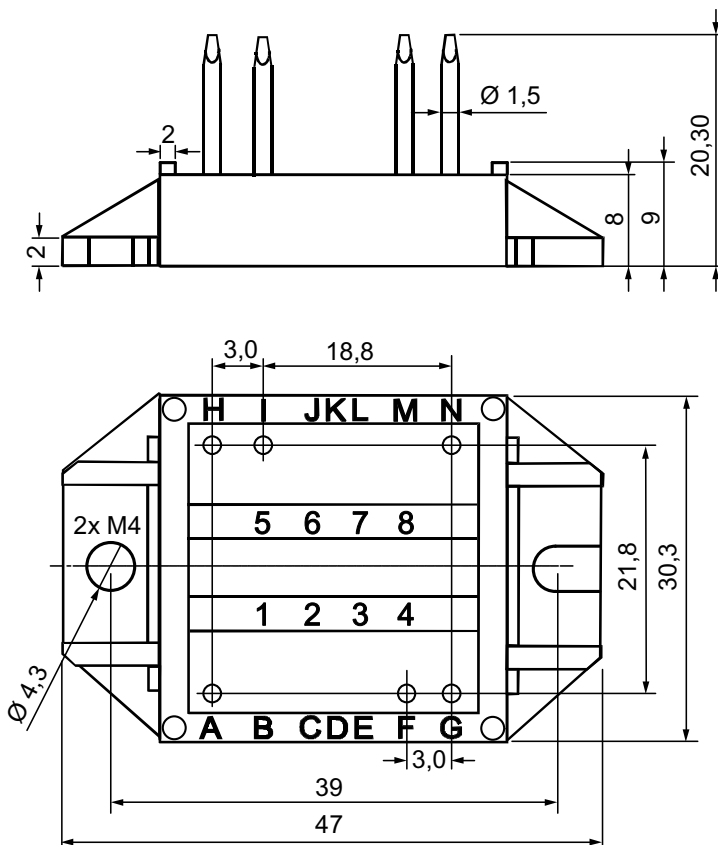
Dimensions in mm (1 mm = 0.0394")


Fig. 2 Gate trigger delay time